

KMM5324000BSW/BSWG Fast Page Mode

4M x 32 DRAM SIMM Using 4Mx16, 4K Refresh, 5V

GENERAL DESCRIPTION

The Samsung KMM5324000B is a 4Mx32bits Dynamic RAM high density memory module. The Samsung KMM5324000B consists of two CMOS 4Mx16bits DRAMs in TSOP packages mounted on a 72-pin glass-epoxy substrate. A 0.1 or 0.22uF decoupling capacitor is mounted on the printed circuit board for each DRAM. The KMM5324000B is a Single In-line Memory Module with edge connections and is intended for mounting into 72 pin edge connector sockets.

PERFORMANCE RANGE

| Speed | t _{RAC} | t _{CAC} | t _{RC} | t _{PC} |
|-------|------------------|------------------|-----------------|-----------------|
| -5 | 50ns | 13ns | 90ns | 35ns |
| -6 | 60ns | 15ns | 110ns | 40ns |

FEATURES

- Part Identification
 - KMM5324000BSW(4K cycles/64ms Ref, TSOP, Solder)
 - KMM5324000BSWG(4K cycles/64ms Ref, TSOP, Gold)
- Fast Page Mode Operation
- $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ & Hidden Refresh capability
- $\overline{\text{RAS}}$ -only refresh capability
- TTL compatible inputs and outputs
- Single +5V±10% power supply
- JEDEC standard PDpin & pinout
- PCB : Height(1000mil), single sided component

PIN CONFIGURATIONS

| Pin | Symbol | Pin | Symbol |
|-----|--------------------------|-----|--------------------------|
| 1 | Vss | 37 | NC |
| 2 | DQ0 | 38 | NC |
| 3 | DQ18 | 39 | Vss |
| 4 | DQ1 | 40 | $\overline{\text{CAS0}}$ |
| 5 | DQ19 | 41 | $\overline{\text{CAS2}}$ |
| 6 | DQ2 | 42 | $\overline{\text{CAS3}}$ |
| 7 | DQ20 | 43 | $\overline{\text{CAS1}}$ |
| 8 | DQ3 | 44 | $\overline{\text{RAS0}}$ |
| 9 | DQ21 | 45 | NC |
| 10 | Vcc | 46 | NC |
| 11 | NC | 47 | $\overline{\text{W}}$ |
| 12 | A0 | 48 | NC |
| 13 | A1 | 49 | DQ9 |
| 14 | A2 | 50 | DQ27 |
| 15 | A3 | 51 | DQ10 |
| 16 | A4 | 52 | DQ28 |
| 17 | A5 | 53 | DQ11 |
| 18 | A6 | 54 | DQ29 |
| 19 | A10 | 55 | DQ12 |
| 20 | DQ4 | 56 | DQ30 |
| 21 | DQ22 | 57 | DQ13 |
| 22 | DQ5 | 58 | DQ31 |
| 23 | DQ23 | 59 | Vcc |
| 24 | DQ6 | 60 | DQ32 |
| 25 | DQ24 | 61 | DQ14 |
| 26 | DQ7 | 62 | DQ33 |
| 27 | DQ25 | 63 | DQ15 |
| 28 | A7 | 64 | DQ34 |
| 29 | A11 | 65 | DQ16 |
| 30 | Vcc | 66 | NC |
| 31 | A8 | 67 | PD1 |
| 32 | A9 | 68 | PD2 |
| 33 | NC | 69 | PD3 |
| 34 | $\overline{\text{RAS2}}$ | 70 | PD4 |
| 35 | NC | 71 | NC |
| 36 | NC | 72 | Vss |

PIN NAMES

| Pin Name | Function |
|---|-----------------------|
| A0 - A11 | Address Inputs |
| DQ0-7, DQ9-16 DQ18-25, DQ27-34 | Data In/Out |
| $\overline{\text{W}}$ | Read/Write Enable |
| $\overline{\text{RAS0}}, \overline{\text{RAS2}}$ | Row Address Strobe |
| $\overline{\text{CAS0}} - \overline{\text{CAS3}}$ | Column Address Strobe |
| PD1 -PD4 | Presence Detect |
| Vcc | Power(+5V) |
| Vss | Ground |
| NC | No Connection |

PRESENCE DETECT PINS (Optional)

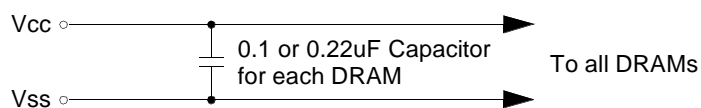
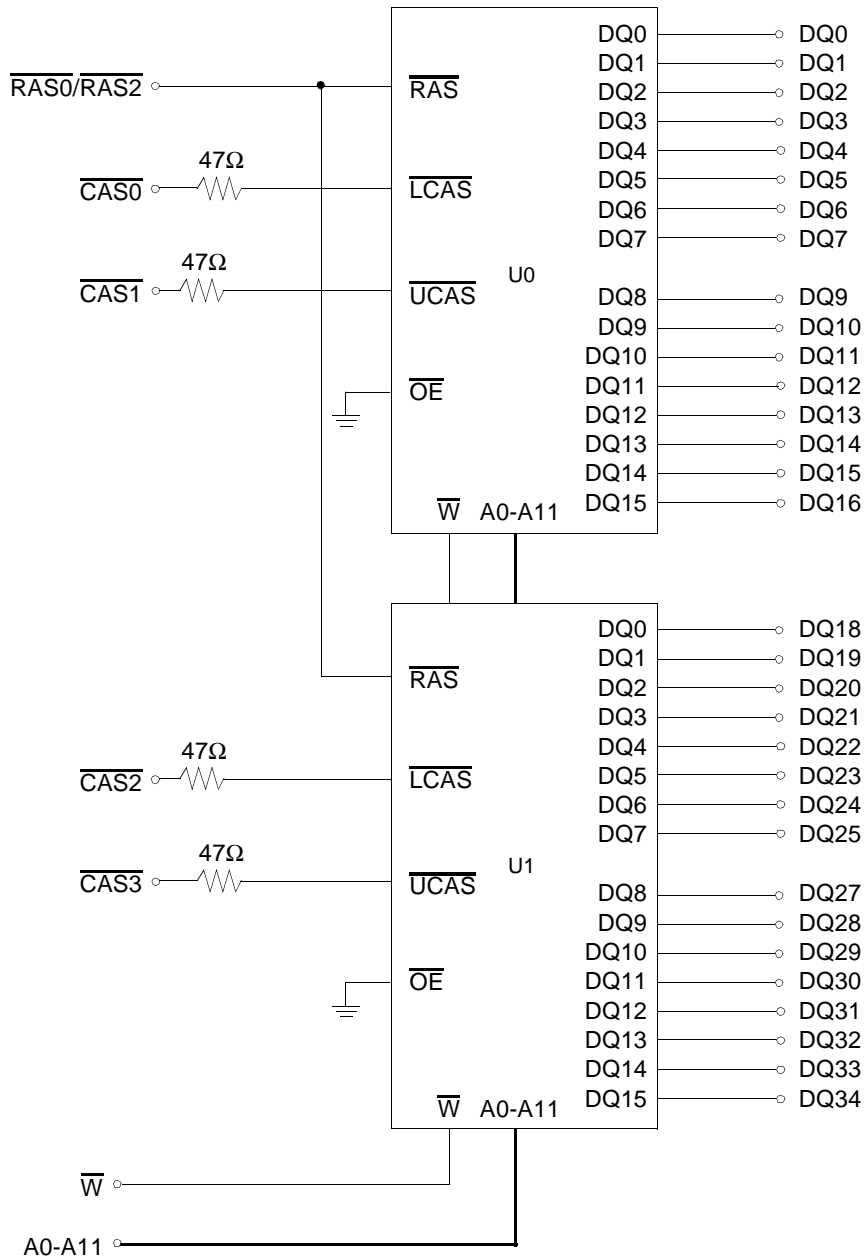
| Pin | 50NS | 60NS |
|-----|------|------|
| PD1 | Vss | Vss |
| PD2 | NC | NC |
| PD3 | Vss | NC |
| PD4 | Vss | NC |

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ELECTRONICS

FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS *

| Item | Symbol | Rating | Unit |
|---------------------------------------|------------------------------------|-------------|------|
| Voltage on any pin relative to VSS | V _{IN} , V _{OUT} | -1 to +7.0 | V |
| Voltage on VCC supply relative to VSS | VCC | -1 to +7.0 | V |
| Storage Temperature | T _{stg} | -55 to +125 | °C |
| Power Dissipation | P _d | 2 | W |
| Short Circuit Output Current | I _{OS} | 50 | mA |

* Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for intended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS (Voltage referenced to VSS, T_A = 0 to 70°C)

| Item | Symbol | Min | Typ | Max | Unit |
|--------------------|-----------------|--------------------|-----|-------------------|------|
| Supply Voltage | VCC | 4.5 | 5.0 | 5.5 | V |
| Ground | VSS | 0 | 0 | 0 | V |
| Input High Voltage | V _{IH} | 2.4 | - | VCC ^{*1} | V |
| Input Low Voltage | V _{IL} | -1.0 ^{*2} | - | 0.8 | V |

*1 : VCC+2.0V at pulse width ≤ 20ns, which is measured at VCC.

*2 : -2.0V at pulse width ≤ 20ns, which is measured at VSS.

DC AND OPERATING CHARACTERISTICS (Recommended operating conditions unless otherwise noted)

| Symbol | Speed | KMM532400BSW/BSWG | | Unit |
|-------------------|------------|-------------------|-----|------|
| | | Min | Max | |
| I _{CC1} | -5 | - | 240 | mA |
| | -6 | - | 220 | mA |
| I _{CC2} | Don't care | - | 4 | mA |
| I _{CC3} | -5 | - | 240 | mA |
| | -6 | - | 220 | mA |
| I _{CC4} | -5 | - | 140 | mA |
| | -6 | - | 120 | mA |
| I _{CC5} | Don't care | - | 2 | mA |
| I _{CC6} | -5 | - | 240 | mA |
| | -6 | - | 220 | mA |
| I _{I(L)} | Don't care | -10 | 10 | uA |
| I _{O(L)} | | -5 | 5 | uA |
| V _{OH} | Don't care | 2.4 | - | V |
| V _{OL} | | - | 0.4 | V |

I_{CC1} : Operating Current * (\overline{RAS} , \overline{CAS} , Address cycling @trc=min)

I_{CC2} : Standby Current ($\overline{RAS}=\overline{CAS}=\overline{W}=V_{IH}$)

I_{CC3} : \overline{RAS} Only Refresh Current * ($\overline{CAS}=V_{IH}$, \overline{RAS} cycling @trc=min)

I_{CC4} : Fast Page Mode Current * ($\overline{RAS}=V_{IL}$, \overline{CAS} cycling : tpc=min)

I_{CC5} : Standby Current ($\overline{RAS}=\overline{CAS}=\overline{W}=V_{CC}-0.2V$)

I_{CC6} : \overline{CAS} -Before- \overline{RAS} Refresh Current * (\overline{RAS} and \overline{CAS} cycling @trc=min)

I_{I(L)} : Input Leakage Current (Any input $0 \leq V_{IN} \leq V_{CC}+0.5V$, all other pins not under test=0 V)

I_{O(L)} : Output Leakage Current(Data Out is disabled, $0V \leq V_{OUT} \leq V_{CC}$)

V_{OH} : Output High Voltage Level (I_{OH} = -5mA)

V_{OL} : Output Low Voltage Level (I_{OL} = 4.2mA)

* **NOTE** : I_{CC1}, I_{CC3}, I_{CC4} and I_{CC6} are dependent on output loading and cycle rates. Specified values are obtained with the output open. I_{CC} is specified as an average current. In I_{CC1} and I_{CC3}, address can be changed maximum once while $\overline{RAS}=V_{IL}$. In I_{CC4}, address can be changed maximum once within one Fast page mode cycle time, tpc.

CAPACITANCE (TA = 25°C, VCC=5V, f = 1MHz)

| Item | Symbol | Min | Max | Unit |
|--|--------|-----|-----|------|
| Input capacitance[A0-A11] | CIN1 | - | 20 | pF |
| Input capacitance[W] | CIN2 | - | 24 | pF |
| Input capacitance[RAS0/RAS2] | CIN3 | - | 24 | pF |
| Input capacitance[CAS0 - CAS3] | CIN4 | - | 17 | pF |
| Input/Output capacitance[DQ0-7, 9-16,18-25, 27-34] | CDQ | - | 17 | pF |

AC CHARACTERISTICS (0°C≤TA≤70°C, VCC=5.0V±10%. See notes 1,2.)

Test condition : VIH/VIL=2.6/0.8V, VOH/VOL=2.4/0.4V, output loading CL=100pF

| Parameter | Symbol | -5 | | -6 | | Unit | Note |
|---|--------|-----|-----|-----|-----|------|--------|
| | | Min | Max | Min | Max | | |
| Random read or write cycle time | tRC | 90 | | 110 | | ns | |
| Access time from $\overline{\text{RAS}}$ | tRAC | | 50 | | 60 | ns | 3,4,10 |
| Access time from $\overline{\text{CAS}}$ | tCAC | | 13 | | 15 | ns | 3,4,5 |
| Access time from column address | tAA | | 25 | | 30 | ns | 3,10 |
| $\overline{\text{CAS}}$ to output in Low-Z | tCLZ | 0 | | 0 | | ns | 3 |
| Output buffer turn-off delay | tOFF | 0 | 13 | 0 | 15 | ns | 6 |
| Transition time(rise and fall) | tT | 1 | 50 | 1 | 50 | ns | 2 |
| $\overline{\text{RAS}}$ precharge time | tRP | 30 | | 40 | | ns | |
| $\overline{\text{RAS}}$ pulse width | tRAS | 50 | 10K | 60 | 10K | ns | |
| $\overline{\text{RAS}}$ hold time | tRSH | 13 | | 15 | | ns | |
| $\overline{\text{CAS}}$ hold time | tCSH | 50 | | 60 | | ns | |
| $\overline{\text{CAS}}$ pulse width | tCAS | 13 | 10K | 15 | 10K | ns | |
| $\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ delay time | tRCD | 20 | 37 | 20 | 45 | ns | 4 |
| $\overline{\text{RAS}}$ to column address delay time | tRAD | 15 | 25 | 15 | 30 | ns | 10 |
| $\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ precharge time | tCRP | 5 | | 5 | | ns | |
| Row address set-up time | tASR | 0 | | 0 | | ns | |
| Row address hold time | tRAH | 10 | | 10 | | ns | |
| Column address set-up time | tASC | 0 | | 0 | | ns | |
| Column address hold time | tCAH | 10 | | 10 | | ns | |
| Column address to $\overline{\text{RAS}}$ lead time | tRAL | 25 | | 30 | | ns | |
| Read command set-up time | tRCS | 0 | | 0 | | ns | |
| Read command hold referenced to $\overline{\text{CAS}}$ | tRCH | 0 | | 0 | | ns | 8 |
| Read command hold referenced to $\overline{\text{RAS}}$ | tRRH | 0 | | 0 | | ns | 8 |
| Write command hold time | tWCH | 10 | | 10 | | ns | |
| Write command pulse width | tWP | 10 | | 10 | | ns | |
| Write command to $\overline{\text{RAS}}$ lead time | tRWL | 15 | | 15 | | ns | |
| Write command to $\overline{\text{CAS}}$ lead time | tCWL | 13 | | 15 | | ns | |
| Data set-up time | tDS | 0 | | 0 | | ns | 9 |
| Data hold time | tDH | 10 | | 10 | | ns | 9 |
| Refresh period | tREF | | 64 | | 64 | ms | |
| Write command set-up time | tWCS | 0 | | 0 | | ns | 7 |
| $\overline{\text{CAS}}$ setup time($\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh) | tCSR | 5 | | 5 | | ns | |
| $\overline{\text{CAS}}$ hold time($\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh) | tCHR | 10 | | 10 | | ns | |
| $\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ precharge time | tRPC | 5 | | 5 | | ns | |
| Access time from $\overline{\text{CAS}}$ precharge | tCPA | | 30 | | 35 | ns | 3 |

AC CHARACTERISTICS (0°C ≤ T_A ≤ 70°C, V_{CC} = 5.0V ± 10%. See notes 1,2.)

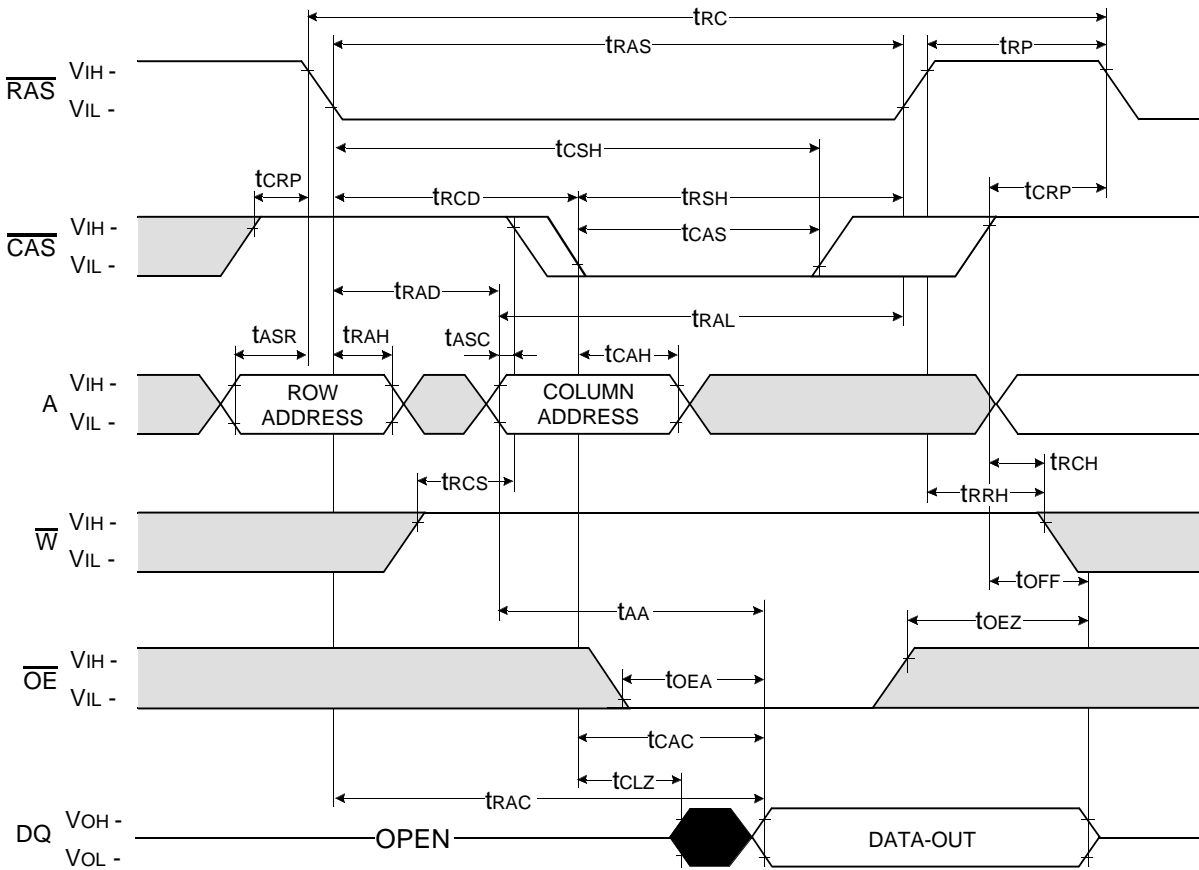
Test condition : V_{ih}/V_{il} = 2.6/0.8V, V_{oh}/V_{ol} = 2.4/0.4V, output loading CL = 100pF

| Parameter | Symbol | -5 | | -6 | | Unit | Note |
|--|-------------------|-----|------|-----|------|------|------|
| | | Min | Max | Min | Max | | |
| Fast page mode cycle time | t _{PC} | 35 | | 40 | | ns | |
| $\overline{\text{CAS}}$ precharge time(Fast page cycle) | t _{CP} | 10 | | 10 | | ns | |
| $\overline{\text{RAS}}$ pulse width(Fast page cycle) | t _{RASP} | 50 | 200K | 60 | 200K | ns | |
| $\overline{\text{W}}$ to $\overline{\text{RAS}}$ precharge time(C-B-R refresh) | t _{WRP} | 10 | | 10 | | ns | |
| $\overline{\text{W}}$ to $\overline{\text{RAS}}$ hold time(C-B-R refresh) | t _{WRH} | 10 | | 10 | | ns | |

NOTES

1. An initial pause of 200us is required after power-up followed by any 8 $\overline{\text{RAS}}$ -only or $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycles before proper device operation is achieved.
2. Input voltage levels are V_{ih}/V_{il}. V_{IH}(min) and V_{IL}(max) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH}(min) and V_{IL}(max) and are assumed to be 5ns for all inputs.
3. Measured with a load equivalent to 2 TTL loads and 100pF.
4. Operation within the t_{RCD}(max) limit insures that t_{RAC}(max) can be met. t_{RCD}(max) is specified as a reference point only. If t_{RCD} is greater than the specified t_{RCD}(max) limit, then access time is controlled exclusively by t_{CAC}.
5. Assumes that t_{RCD} ≥ t_{RCD}(max).
6. This parameter defines the time at which the output achieves the open circuit condition and is not referenced to V_{OH} or V_{OL}.
7. twcs is non-restrictive operating parameter. It is included in the data sheet as electrical characteristics only. If twcs ≥ twcs(min), the cycle is an early write cycle and the data out pin will remain high impedance for the duration of the cycle.
8. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
9. These parameters are referenced to the $\overline{\text{CAS}}$ leading edge in early write cycles.
10. Operation within the t_{RAD}(max) limit insures that t_{RAC}(max) can be met. t_{RAD}(max) is specified as reference point only. If t_{RAD} is greater than the specified t_{RAD}(max) limit, then access time is controlled by t_{AA}.

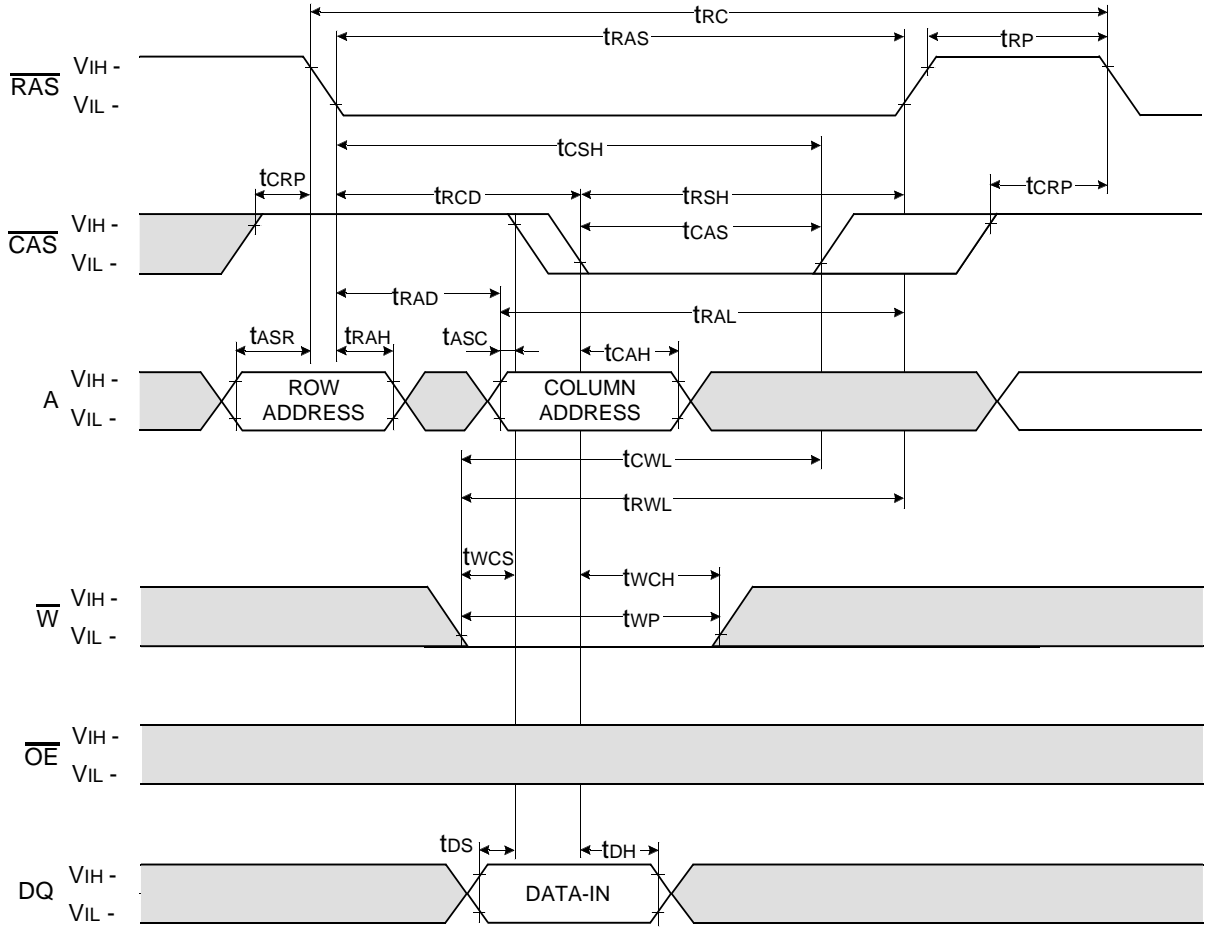
READ CYCLE



Don't care
 Undefined

WRITE CYCLE (EARLY WRITE)

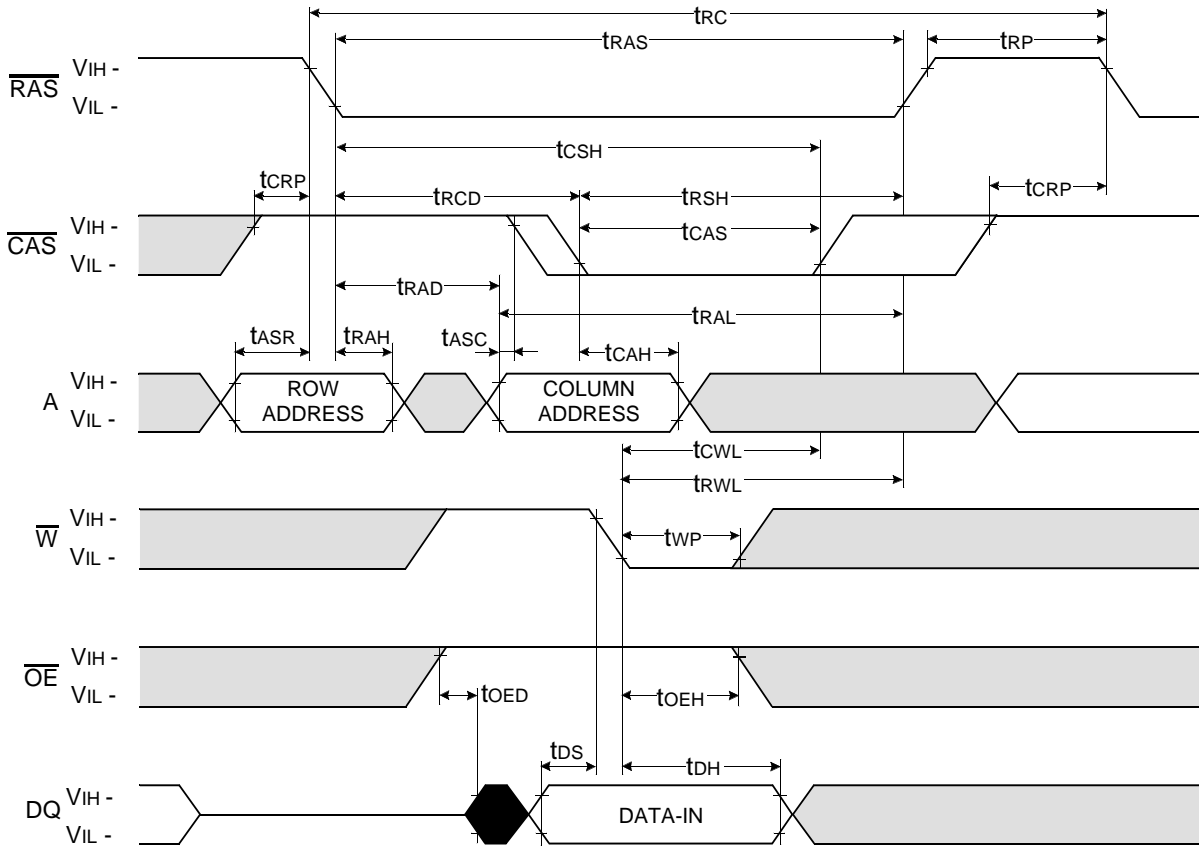
NOTE : DOUT = OPEN



□ Don't care
■ Undefined

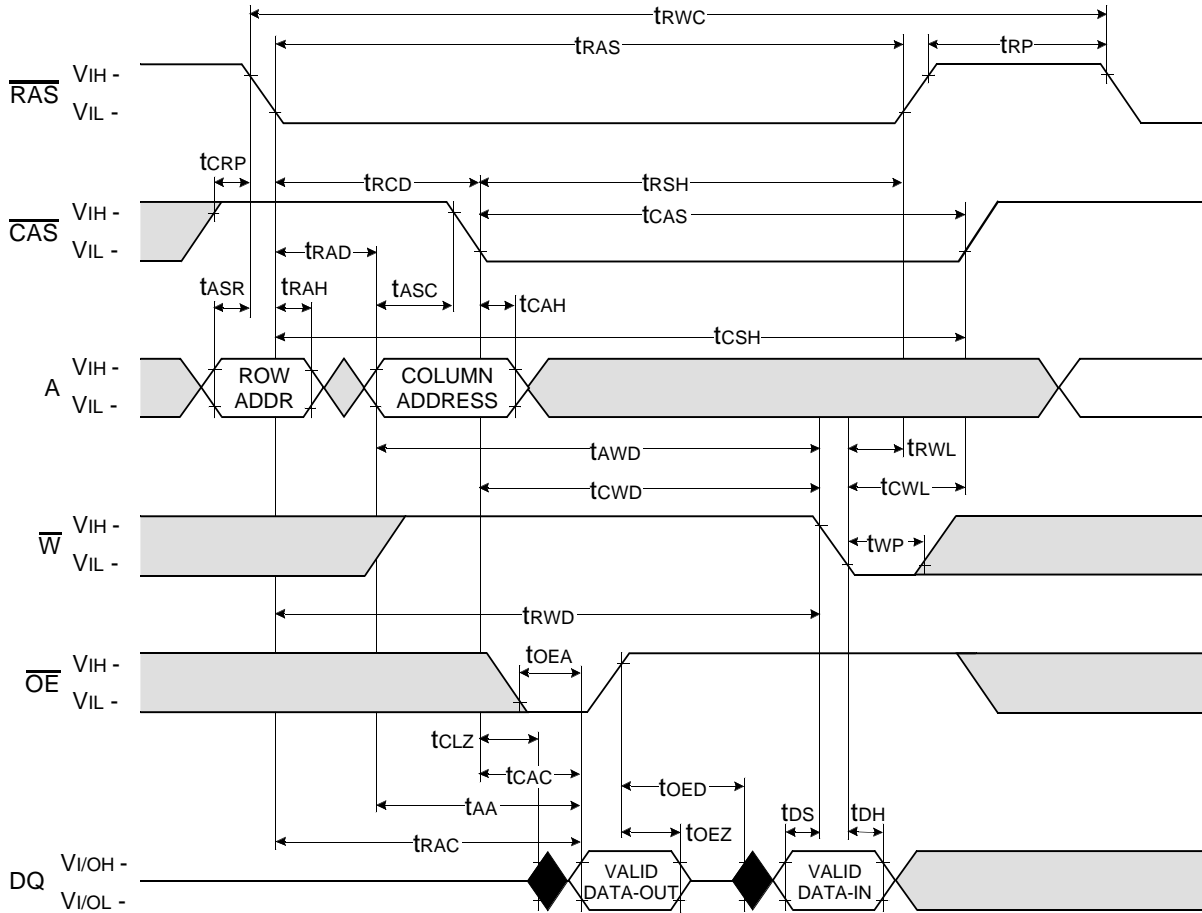
WRITE CYCLE (\overline{OE} CONTROLLED WRITE)

NOTE : DOUT = OPEN



□ Don't care
■ Undefined

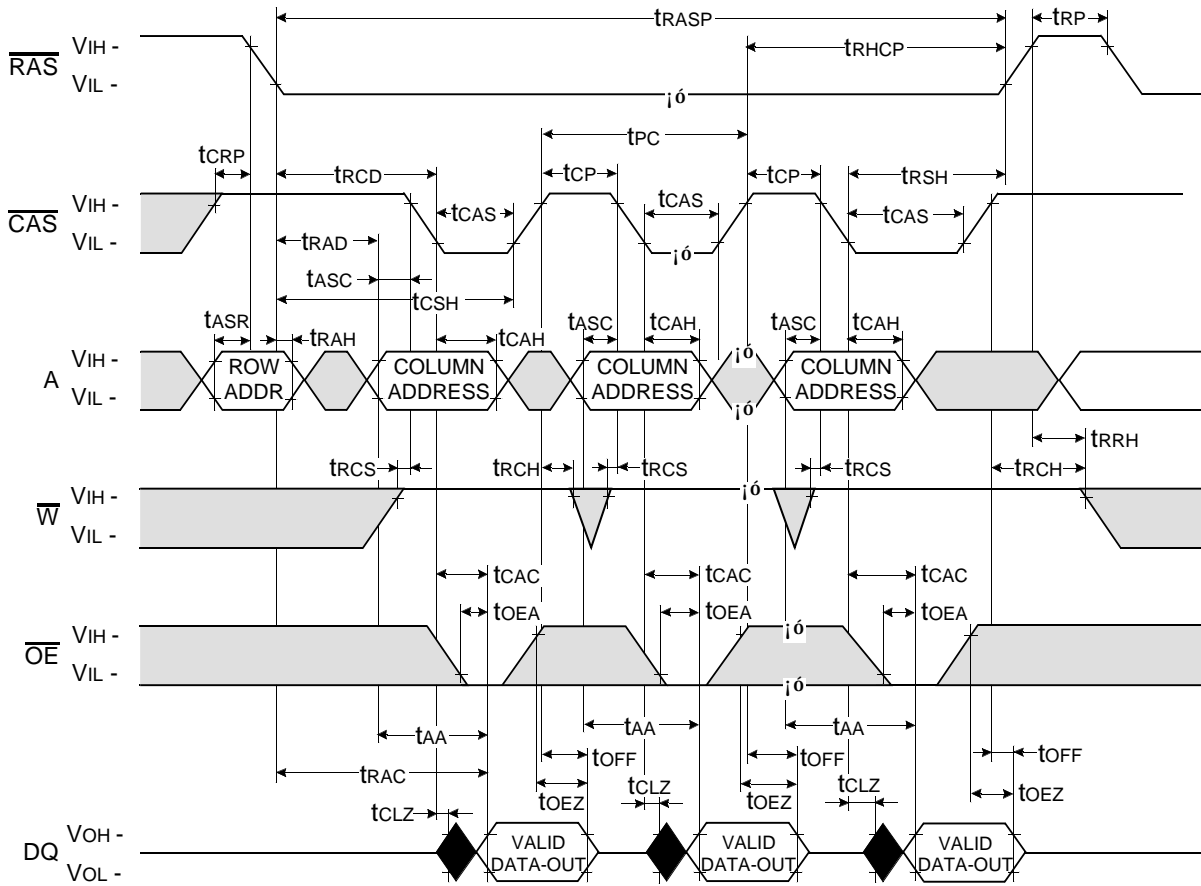
READ - MODIFY - WRITE CYCLE



Don't care
 Undefined

FAST PAGE READ CYCLE

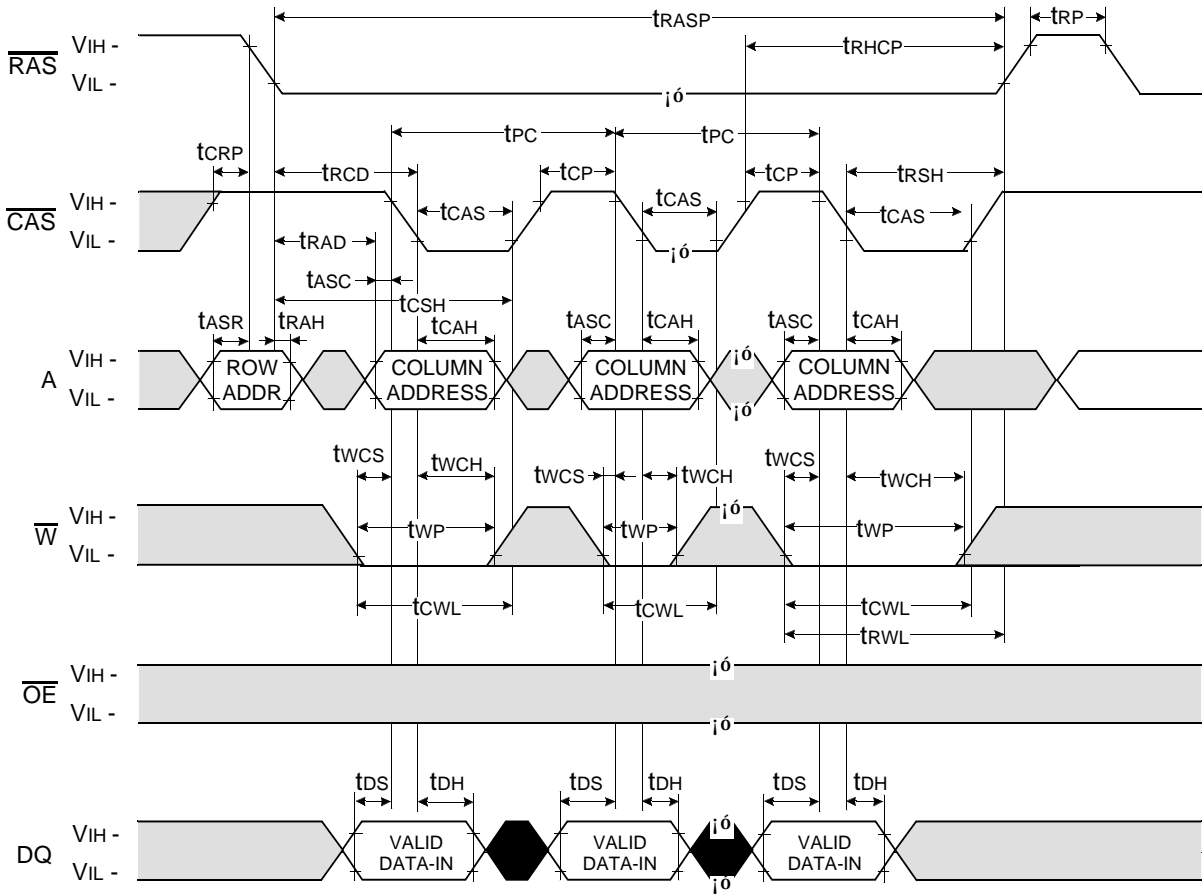
NOTE : DOUT = OPEN



□ Don't care
 ■ Undefined

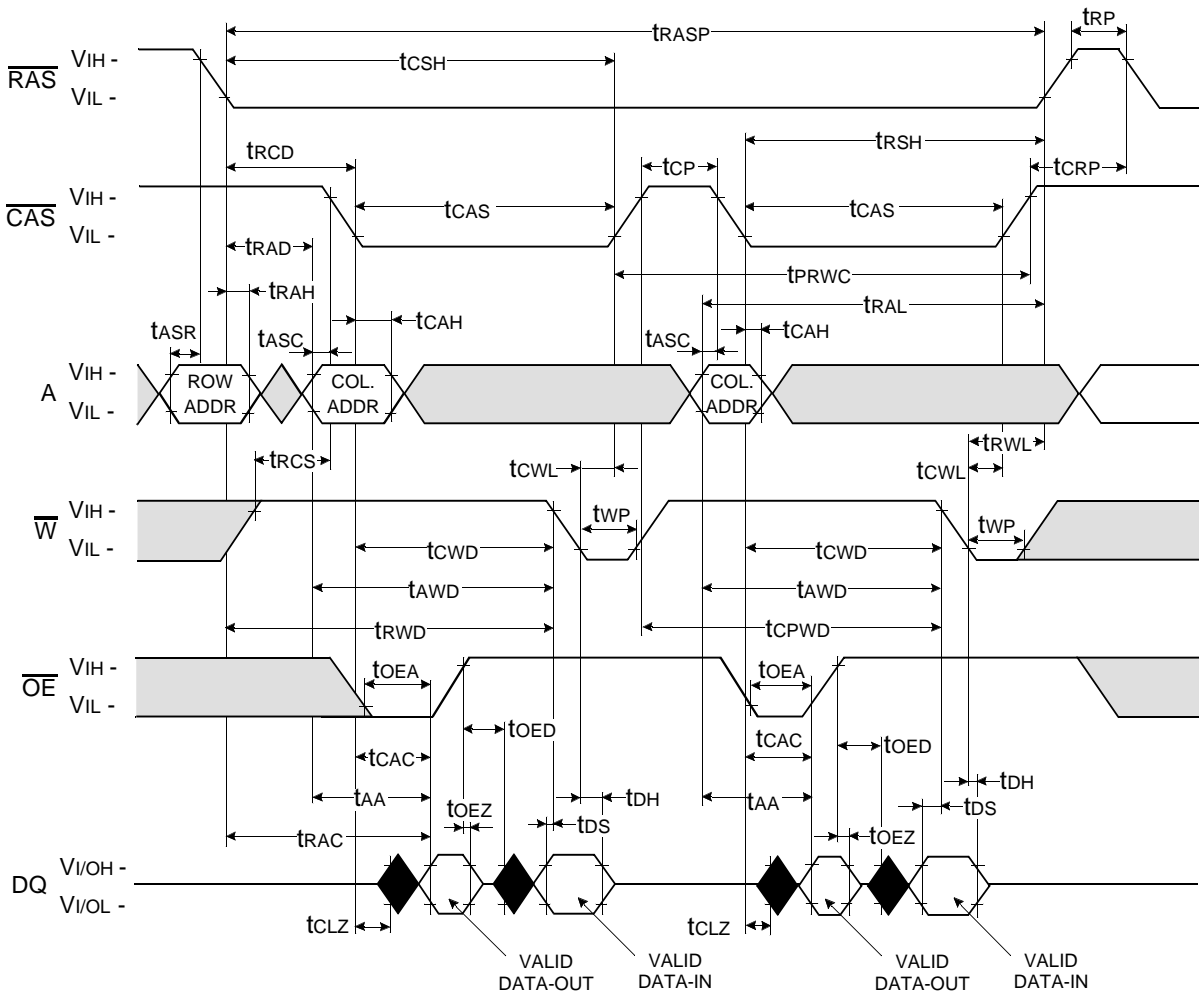
FAST PAGE WRITE CYCLE (EARLY WRITE)

NOTE : DOUT = OPEN



Don't care
 Undefined

FAST PAGE READ - MODIFY - WRITE CYCLE

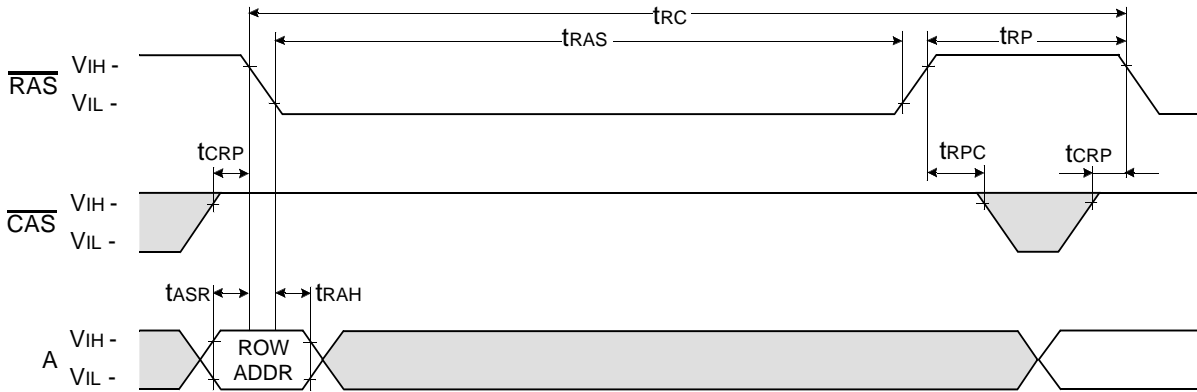


Don't care
 Undefined

$\overline{\text{RAS}}$ - ONLY REFRESH CYCLE

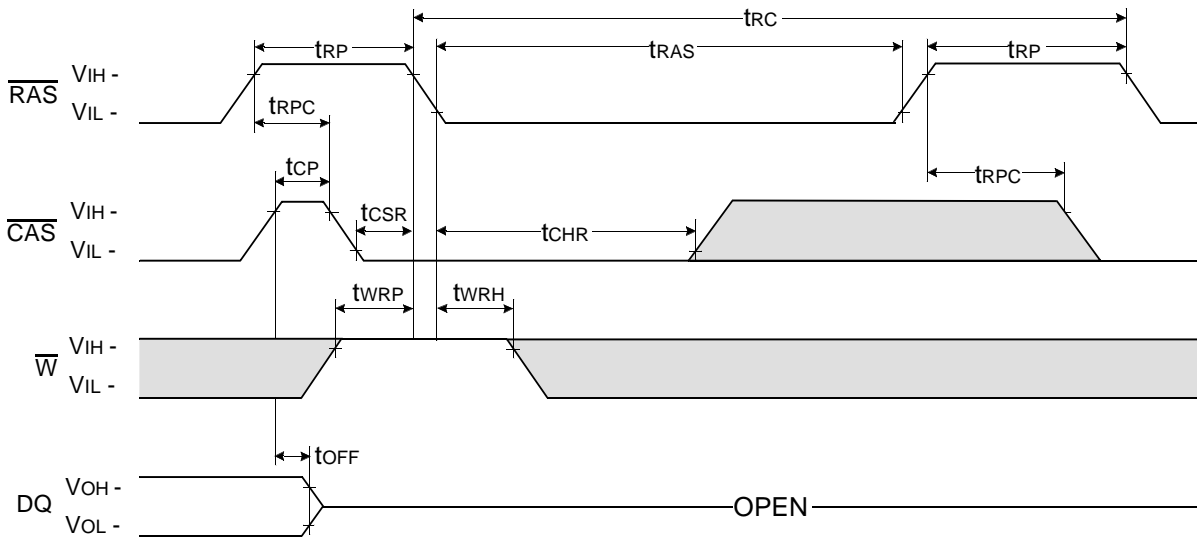
NOTE : $\overline{\text{W}}$, $\overline{\text{OE}}$, DIN = Don't care

DOUT = OPEN



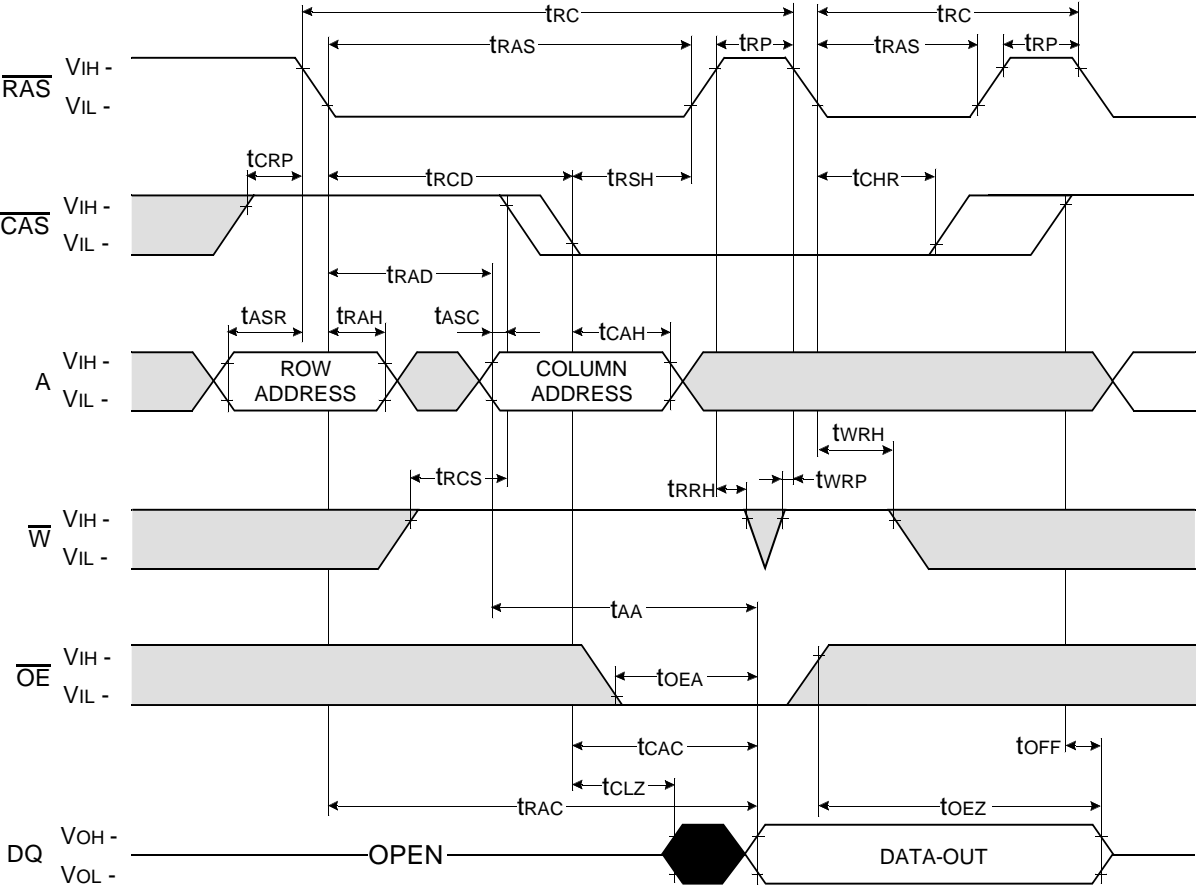
$\overline{\text{CAS}}$ - BEFORE - $\overline{\text{RAS}}$ REFRESH CYCLE

NOTE : $\overline{\text{OE}}$, A = Don't care



□ Don't care
 ■ Undefined

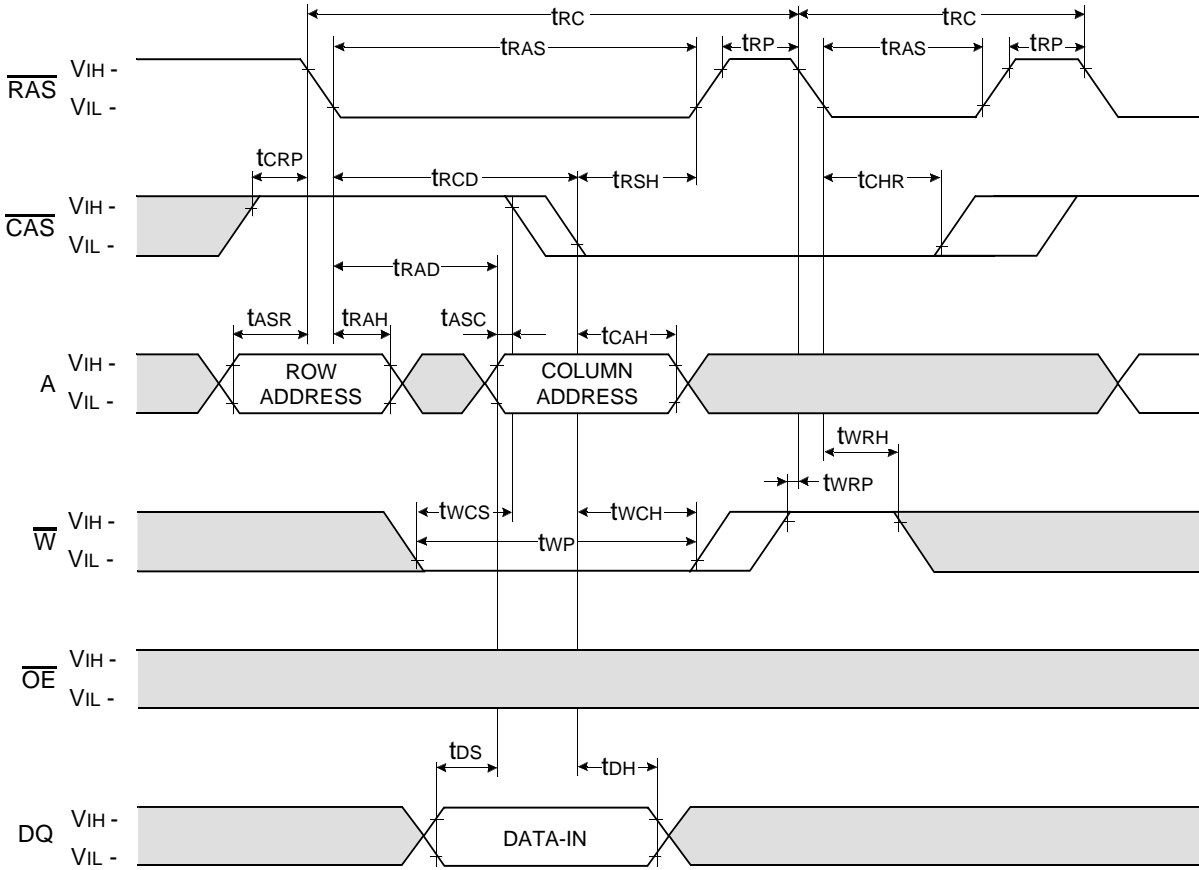
HIDDEN REFRESH CYCLE (READ)



□ Don't care
■ Undefined

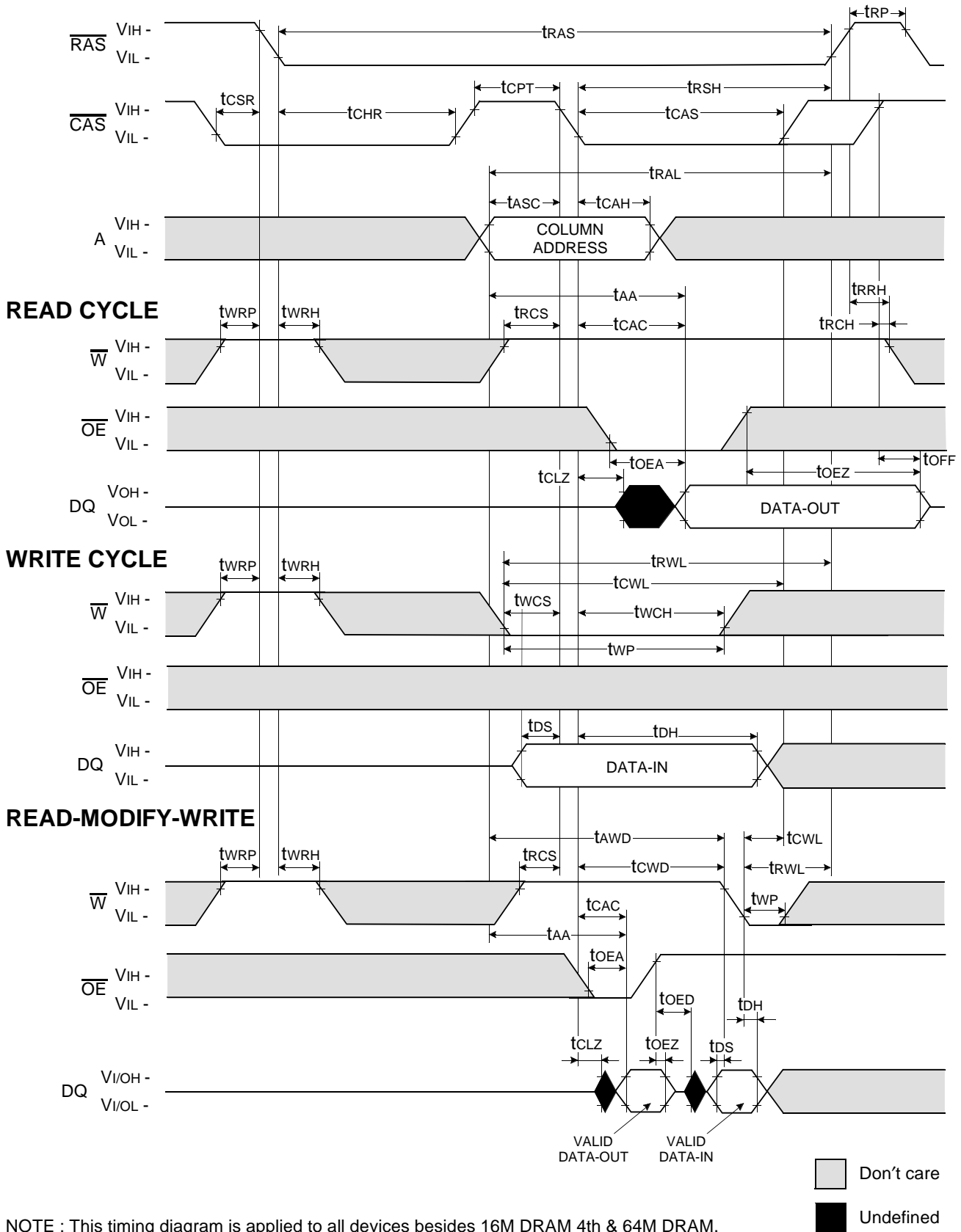
HIDDEN REFRESH CYCLE (WRITE)

NOTE : DOUT = OPEN



□ Don't care
■ Undefined

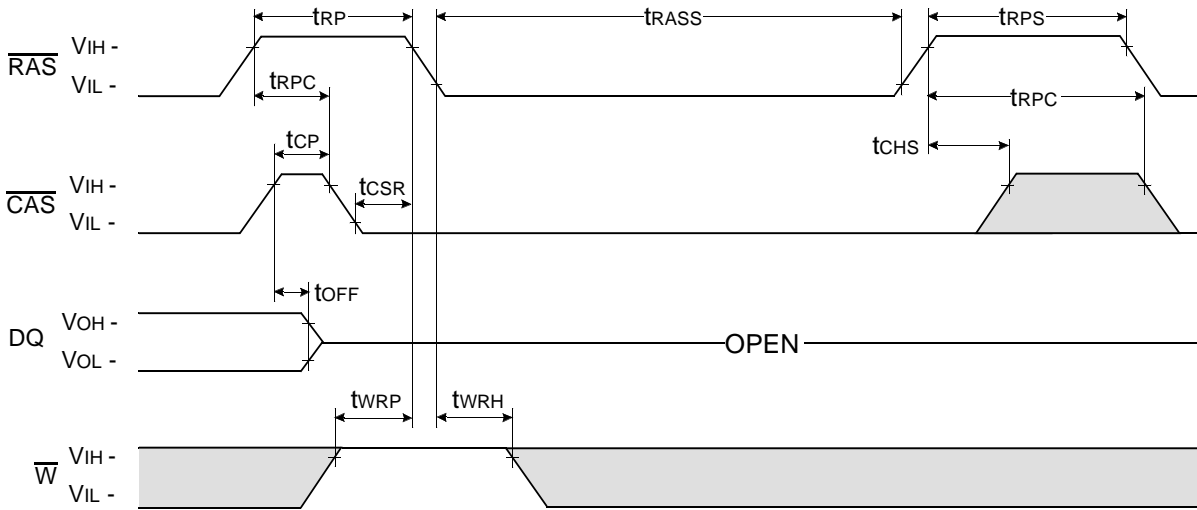
CAS-BEFORE-RAS REFRESH COUNTER TEST CYCLE



NOTE : This timing diagram is applied to all devices besides 16M DRAM 4th & 64M DRAM.

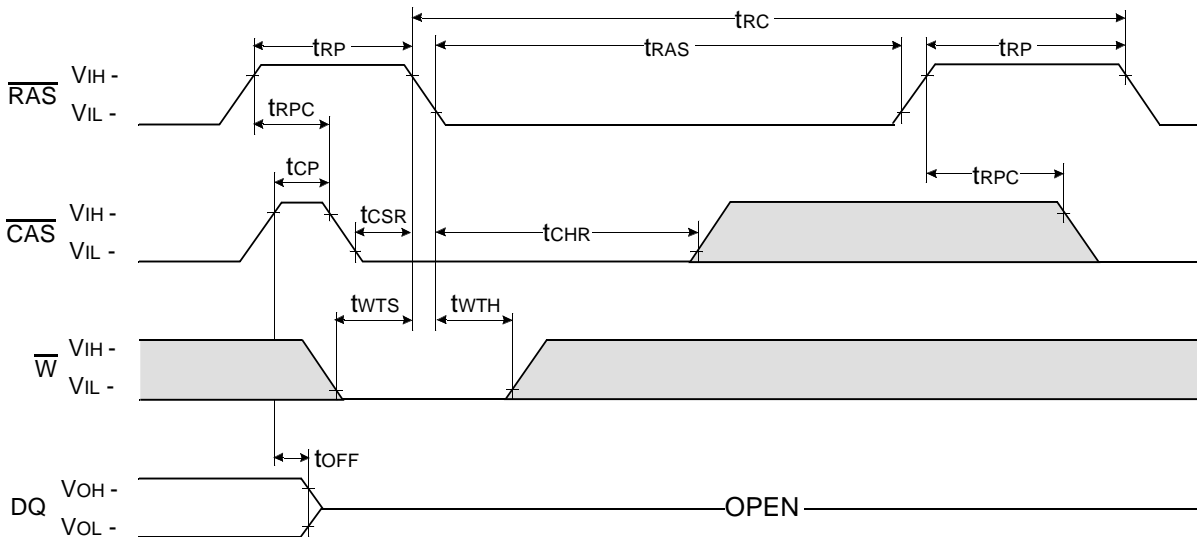
$\overline{\text{CAS}}$ - BEFORE - $\overline{\text{RAS}}$ SELF REFRESH CYCLE

NOTE : $\overline{\text{OE}}$, A = Don't care



TEST MODE IN CYCLE

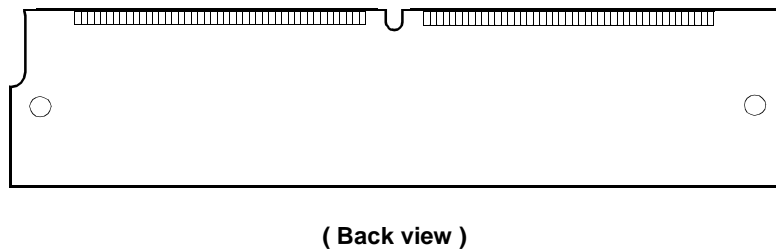
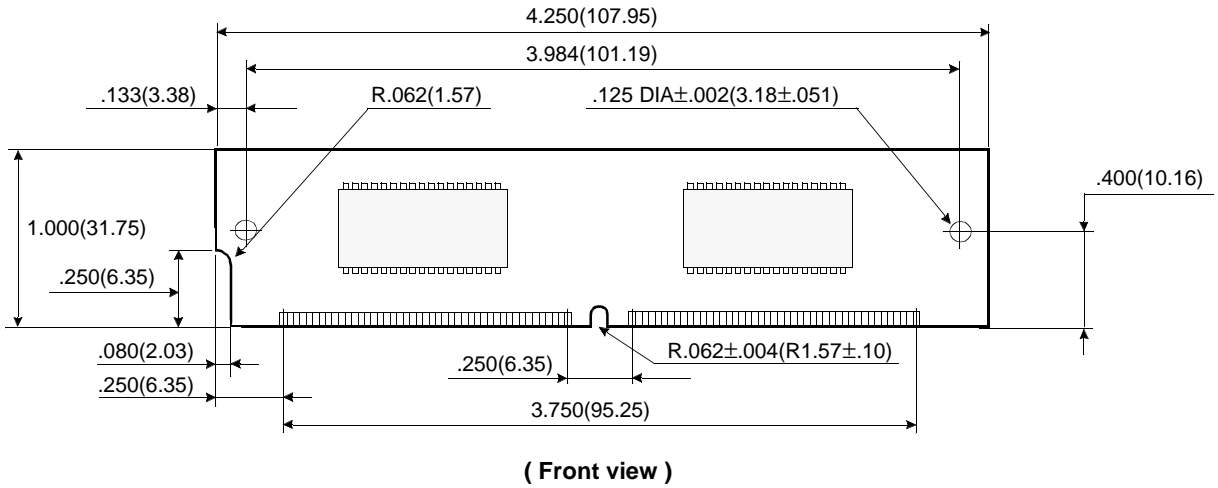
NOTE : $\overline{\text{OE}}$, A = Don't care



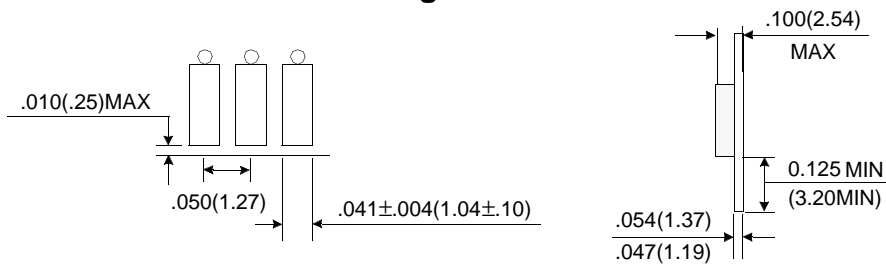
□ Don't care
 ■ Undefined

PACKAGE DIMENSIONS

Units : Inches (millimeters)



Gold/Solder Plating Lead



Tolerances : $\pm .005(.13)$ unless otherwise specified

NOTE : The used device is 4Mx16 DRAM, TSOPII
 DRAM Part No. : KMM532400BSW/BSWG -- KM416C4100BS